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ABSTRACT

A transistor has a source electrode and a drain electrode formed with a predetermined interval secured in between on a semiconductor layer formed to perspective overlap a gate electrode. The source and drain electrodes are each longer in their lengthwise direction than in their widthwise direction. The source electrode has a recessed portion formed therein to allow the tip portion of the drain electrode in. The semiconductor layer protrudes out of the gate electrode to form a portion that does not overlap the gate electrode but overlaps the source electrode and a portion that does not overlap the gate electrode but overlaps the drain electrode. Thus, the protruding portion that overlaps the source electrode and the protruding portion that overlaps the drain electrode are separated from each other by the gate electrode so as to be independent of each other. This prevents short-circuiting between the source and drain that results when the portions of the semiconductor islands protruding out of the gate electrode become conductive through a photoelectric effect brought about by the light that travels past the gate electrode or by another cause.

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